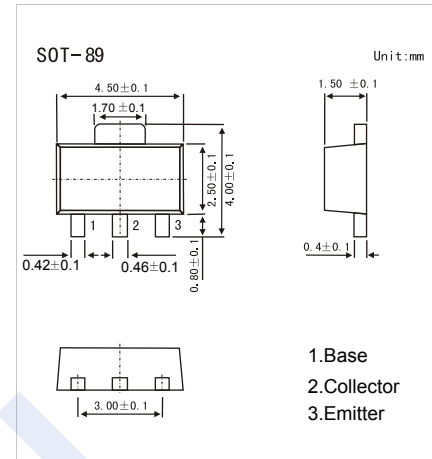


## NPN Transistors

## 2SC5026

## ■ Features

- Low collector to emitter saturation voltage  $V_{CE(sat)}$ .
- High collector to emitter voltage  $V_{CEO}$ .
- Complementary to 2SA1890

■ Absolute Maximum Ratings  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	$V_{CBO}$	80	V
Collector - Emitter Voltage	$V_{CEO}$	80	
Emitter - Base Voltage	$V_{EBO}$	5	
Collector Current - Continuous	$I_C$	1	A
Collector Current - Pulse	$I_{CP}$	1.5	
Collector Power Dissipation	$P_C$	1	W
Junction Temperature	$T_J$	150	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-55 to 150	

■ Electrical Characteristics  $T_a = 25^\circ\text{C}$ 

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	$V_{CBO}$	$I_C = 100 \mu\text{A}, I_E = 0$	80			V
Collector- emitter breakdown voltage	$V_{CEO}$	$I_C = 1 \text{ mA}, I_B = 0$	80			
Emitter - base breakdown voltage	$V_{EBO}$	$I_E = 100 \mu\text{A}, I_C = 0$	5			
Collector-base cut-off current	$I_{CBO}$	$V_{CB} = 60\text{V}, I_E = 0$			0.1	$\mu\text{A}$
Emitter cut-off current	$I_{EBO}$	$V_{EB} = 4\text{V}, I_C = 0$			0.1	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$		0.15	0.3	V
Base - emitter saturation voltage	$V_{BE(sat)}$	$I_C = 500\text{mA}, I_B = 50\text{mA}$		0.85	1.2	
DC current gain	$h_{FE}$	$V_{CE} = 2\text{V}, I_C = 100\text{mA}$	120		340	
		$V_{CE} = 2\text{V}, I_C = 500\text{mA}$	60			
Collector output capacitance	$C_{ob}$	$V_{CB} = 10\text{V}, I_E = 0, f = 1\text{MHz}$		10	20	$\text{pF}$
Transition frequency	$f_T$	$V_{CE} = 10\text{V}, I_E = -50\text{mA}, f = 200\text{MHz}$		120		$\text{MHz}$

■ Classification of  $h_{FE(1)}$ 

Type	2SC5026-R	2SC5026-S
Range	120-240	170-340
Marking	2AR	2AS

## NPN Transistors 2SC5026

■ Typical Characteristics

